Effect of Chemical Treatment on Electrophysical Characteristics of In/p-PbTe/In Structures

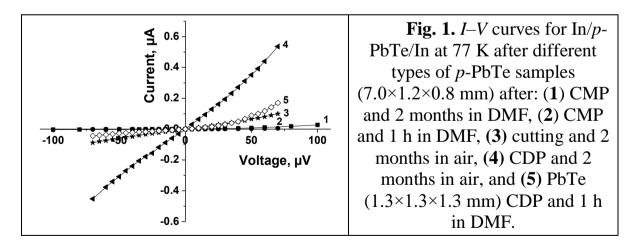
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Lead telluride is used for the manufacture of injection lasers in the 3-5 μ m spectrum, as well as in thermoelectricity. The efficiency of devices based on lead telluride largely depends on the quality of electrical contacts.

In our experiments, the Bridgman-grown no crystallographic oriented single crystals of PbTe have been used. The PbTe characterictics – *p*-type, $[p] = 1.5 \times 10^{18} \text{ cm}^{-3}$, $\mu_p = 650 \text{ cm}^2/(\text{V} \times \text{s})$, undoped. Technological scheme of PbTe plates processing with etching composition H₂O₂ + HBr + EG is given in [1]. Contacts have been formed on chemically etched surface of *p*-PbTe single crystals by the thermal vacuum deposition method. Pre-deposition surface treatment produced interfaces free from oxide layers. All measurements of the *I*-*V* characteristics were carried out by the *dc* method in the temperature range 77–295 K on PbTe samples after cutting, chemical-mechanical polishing (CMP) and chemical-dynamic polishing (CDP).

Measurements the I-V characteristics of In/p-PbTe/In structures were performed at temperatures of 77 K and 292 K. It should be noted the linearity of the corresponding I-V characteristics at 292 K. From Fig. 1, it can be seen that at low temperatures, the I-V characteristic deviates from linearity.



[1]. Malanych G.P., Stanetska A.S., Stratiychuk I.B., Tomashyk V.M. Technological scheme of mechanical and chemical treatment of PbTe and Pb_{1-x}Sn_xTe solid solutions for obtaining polished surface of single crystal. *Materials Today: Proceedings*. 2021. V. 35, Part 3. P. 558-562.